2N3906

General Purpose Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	40	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	Ic	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Power Dissipation @ T _A = 60°C	P _D	250	mW
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

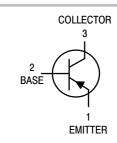
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

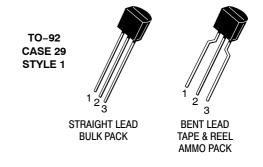
1. Indicates Data in addition to JEDEC Requirements.



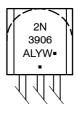
ON Semiconductor®

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MARKING DIAGRAM



A = Assembly Location

= Wafer Lot

Y = Year

W = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N3906

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

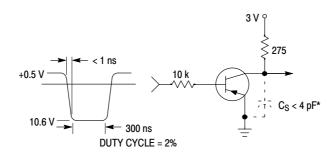
	Symbol	Min	Max	Unit		
OFF CHARACTERIS	TICS				•	
Collector - Emitter Br	eakdown Voltage (Note 2)	$(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	40	-	Vdc
Collector - Base Brea	kdown Voltage	$(I_C = 10 \mu Adc, I_E = 0)$	V _{(BR)CBO}	40	-	Vdc
Emitter - Base Break	down Voltage	$(I_E = 10 \mu Adc, I_C = 0)$	V _{(BR)EBO}	5.0	_	Vdc
Base Cutoff Current		(V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	-	50	nAdc
Collector Cutoff Curre	ent	(V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc
ON CHARACTERIST	TICS (Note 2)			•		-
DC Current Gain		h _{FE}	60 80 100 60 30	- 300 - -	_	
Collector - Emitter Sa	turation Voltage	$(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{CE(sat)}	- -	0.25 0.4	Vdc
Base – Emitter Satura	ition Voltage	$(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CH	IARACTERISTICS					
Current-Gain - Ban	dwidth Product (I _C	= 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	250	-	MHz
Output Capacitance		(V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	4.5	pF
Input Capacitance		(V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	10	pF
Input Impedance	(I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{ie}	2.0	12	kΩ
Voltage Feedback Ra	atio (I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{re}	0.1	10	X 10 ⁻⁴
Small-Signal Current	Gain (I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{fe}	100	400	-
Output Admittance	(I _C	= 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	h _{oe}	3.0	60	μmhos
Noise Figure	(I _C = 100 μAdc, \	$V_{CE} = 5.0 \text{ Vdc}, R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz}$	NF	-	4.0	dB
SWITCHING CHARA	CTERISTICS					
Delay Time (V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	-	35	ns	
Rise Time	$I_C = 10 \text{ mAdc}, I_{B1} = 1.0$		t _r	-	35	ns
Storage Time	(V _{CC} = 3.0 Vdc, I _C = 10	0 mAdc, I _{B1} = I _{B2} = 1.0 mAdc)	t _s	-	225	ns
Fall Time	(V _{CC} = 3.0 Vdc, I _C = 10	0 mAdc, I _{B1} = I _{B2} = 1.0 mAdc)	t _f	-	75	ns

^{2.} Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

ORDERING INFORMATION

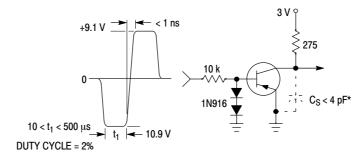
Device	Package	Shipping [†]
2N3906	TO-92	5000 Units / Bulk
2N3906G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3906RL1	TO-92	2000 / Tape & Reel
2N3906RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3906RLRA	TO-92	2000 / Tape & Reel
2N3906RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3906RLRM	TO-92	2000 / Tape & Ammo Box
2N3906RLRMG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
2N3906RLRP	TO-92	2000 / Tape & Ammo Box
2N3906RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



^{*} Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

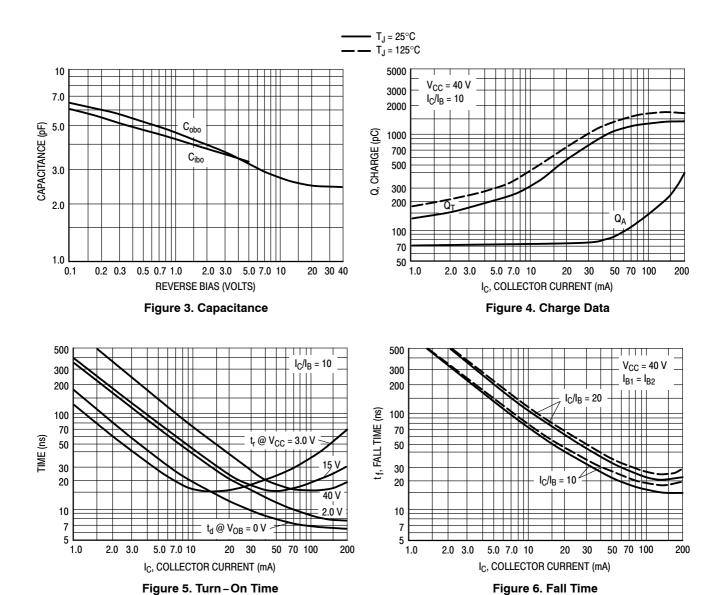


^{*} Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

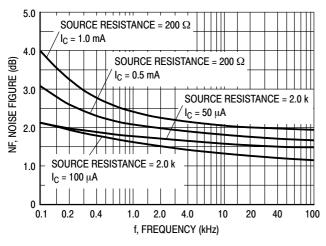
2N3906

TYPICAL TRANSIENT CHARACTERISTICS



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS **NOISE FIGURE VARIATIONS**

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



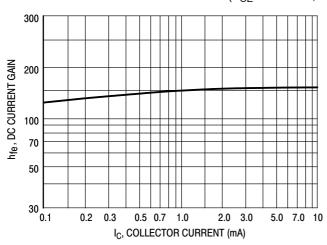
12 f = 1.0 kHz10 NF, NOISE FIGURE (dB) I_C = 50 μ A $I_C = 100 \mu A$ 0.2 2.0 4.0 0.4 1.0 10 20 40 0.1 100 R_q, SOURCE RESISTANCE (k OHMS)

Figure 7.

Figure 8.

h PARAMETERS

($V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C}$)



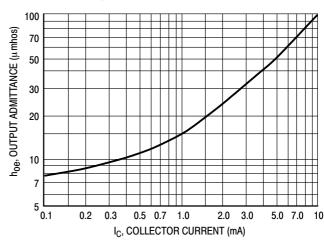
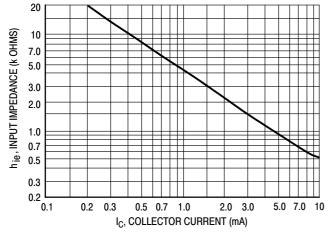


Figure 9. Current Gain

Figure 10. Output Admittance



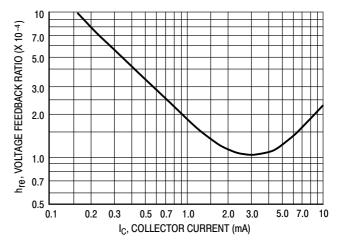


Figure 11. Input Impedance

Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

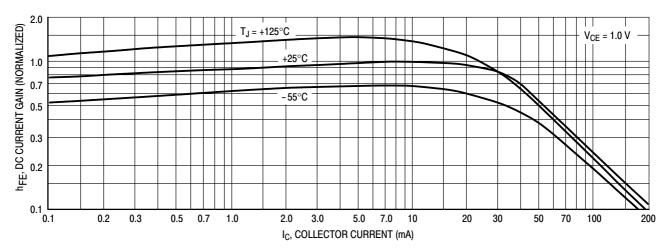


Figure 13. DC Current Gain

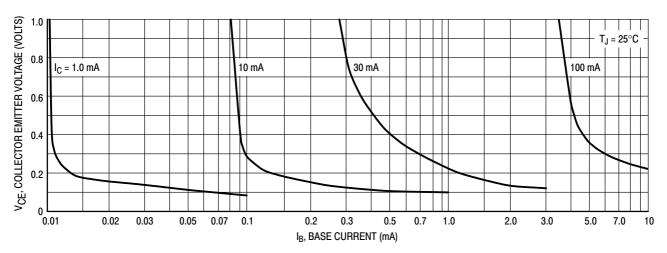


Figure 14. Collector Saturation Region

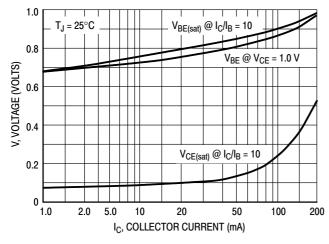


Figure 15. "ON" Voltages

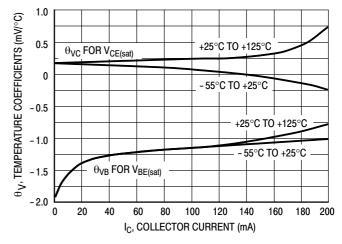
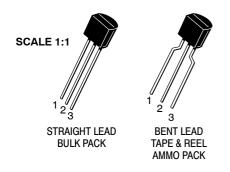
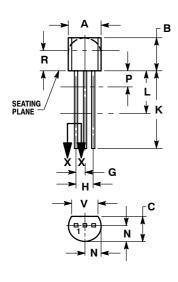


Figure 16. Temperature Coefficients



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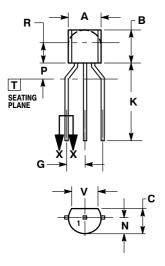


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AND IDECRANGING FER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500	-	12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

- - MILLIMETERS
 MIN MAX A 4.45 B 4.32 5.20 5.33 3.18 0.40 2.40 0.54 2.80 0.39 0.50 2.66 2.04 1.50 N 4.00 2.93

V 3.43

STYLES ON PAGE 2

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STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE		
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE
2. 3.	CATHODE & ANODE CATHODE	2. 3.	GATE MAIN TERMINAL 2	2. 3.		2. 3.	COLLECTOR BASE	2. 3.	CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
PIN 1. 2.	COLLECTOR EMITTER BASE	PIN 1	SOURCE	PIN 1.	GATE SOURCE DRAIN	PIN 1.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1.	MT 1
	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE SOURCE
2.	GATE DRAIN SOURCE	2.	COLLECTOR	STYLE 33: PIN 1. 2. 3.	INPUT	2.	INPUT GROUND LOGIC	STYLE 35: PIN 1. 2. 3.	GATE

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NTE15 NTE16001